

Fig. 1 Real time thickness variation as a function of Ar exposure time for the SiO₂ ALE at 20 °C (RT) and -20 °C (LT).

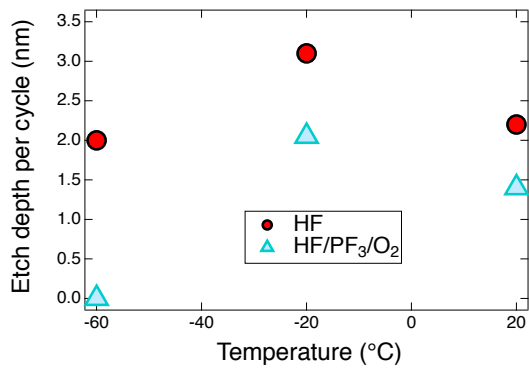


Fig. 2 Dependence of etch depth per cycle on substrate temperature of the SiN ALE with surface modification step of HF and HF/PF₃/O₂ plasma.